

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-8TQ080GSTRLPBF</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-8TQ080GSTRLPBF - DIODE GEN PURPOSE 80V 8A D2PAK

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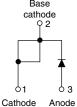


VS-8TQ...GPbF Series, VS-8TQ...G-N3 Series

Vishay Semiconductors

Schottky Rectifier, 8 A





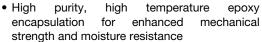
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01	03
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Cathode	Anode

PRODUCT SUMMARY					
Package	TO-220AC				
I _{F(AV)}	8 A				
V_{R}	80 V, 100 V				
V _F at I _F	0.58 V				
I _{RM} max.	7 mA at 125 °C				
T _J max.	175 °C				
Diode variation	Single die				
E _{AS}	7.5 mJ				

FEATURES

- 175 °C T_J operation
- · Low forward voltage drop
- High frequency operation





- · Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION

The VS-8TQ...G Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL CHARACTERISTICS VALUES UNITS							
I _{F(AV)}	Rectangular waveform	8	А				
V _{RRM}		100	V				
I _{FSM}	t _p = 5 μs sine	850	А				
V _F	8 A _{pk} , T _J = 125 °C	0.58	V				
T _J	Range	- 55 to 175	°C				

VOLTAGE RATINGS									
PARAMETER	SYMBOL	VS-8TQ080GPbF	VS-8TQ080G-N3	VS-8TQ100GPbF	VS-8TQ100G-N3	UNITS			
Maximum DC reverse voltage	V _R	80	90	100	100	V			
Maximum working peak reverse voltage	V _{RWM}	00	80	100	100				

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST COND	ITIONS	VALUES	UNITS		
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T _C = 157 °C	8				
Maximum peak one cycle non-repetitive surge current	I _{FSM}	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated	850	Α		
See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	230			
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 0.50 A, L = 60 mH		7.50	mJ		
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero Frequency limited by T_J maxim		0.50	Α		

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ELECTRICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS		
Maximum forward voltage drop See fig. 1		8 A	T _ 05 °C	0.72	V		
	V _{FM} ⁽¹⁾	16 A	$T_J = 25 ^{\circ}\text{C}$	0.88			
	VFM (17	8 A	T _{.1} = 125 °C	0.58			
		16 A	- IJ = 125 C	0.69			
Maximum reverse leakage curent	I _{RM} ⁽¹⁾	T _J = 25 °C	V D-tIV	0.28	mA		
See fig. 2	IRM ('')	T _J = 125 °C	V_R = Rated V_R	7			
Maximum junction capacitance	C _T	V _R = 5 V _{DC} (test signal range 100 kHz to 1 MHz) 25 °C		500	pF		
Typical series inductance	L _S	Measured lead to lead 5 mm from package body		8	nH		
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs		

Note

 $^{^{(1)}\,}$ Pulse width < 300 $\mu s,\,duty\,\,cycle < 2\,\,\%$

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 55 to 175	°C			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation See fig. 4	2.0	°C/W			
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.50	°C/VV			
Approximate weight			2	g			
Approximate weight			0.07	OZ.			
Mounting torque minimum			6 (5)	kgf · cm			
maximum			12 (10)	(lbf · in)			
Marking dayion		Casa atula TO 220AC	8TQ(080G			
Marking device		Case style TO-220AC	8TQ100G				



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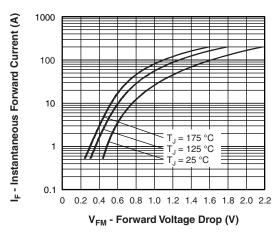


Fig. 1 - Maximum Forward Voltage Drop Characteristics

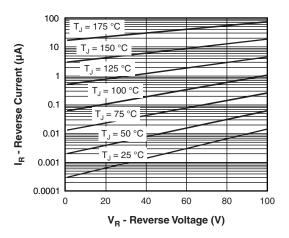


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

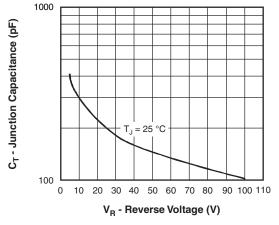


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

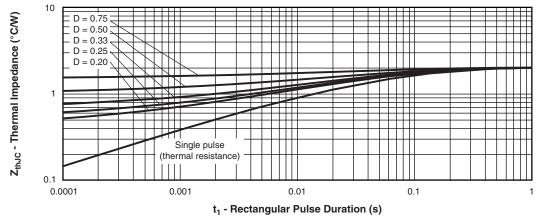


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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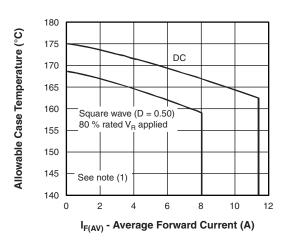


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

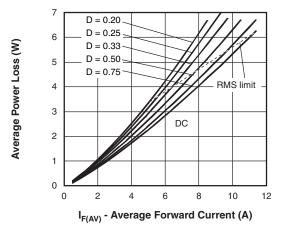


Fig. 6 - Forward Power Loss Characteristics

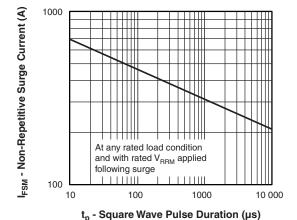


Fig. 7 - Maximum Non-Repetitive Surge Current

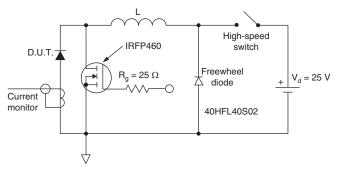


Fig. 8 - Unclamped Inductive Test Circuit

Note

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)}x$ V_{FM} at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1}x$ I_{R} (1 - D); I_{R} at V_{R1} = 80 % rated V_{R}

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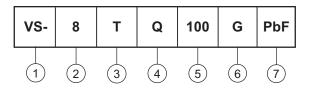


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Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Current rating (8 = 8 A)

T = TO-220

Q = Schottky "Q" series

Voltage rating (100 = 100 V)

G = Schottky generation

Environmental digit

• PbF = Lead (Pb)-free and RoHS compliant

• -N3 = Halogen-free, RoHS compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-8TQ080GPbF	50	1000	Antistatic plastic tube				
VS-8TQ080G-N3	50	1000	Antistatic plastic tube				
VS-8TQ100GPbF	50	1000	Antistatic plastic tube				
VS-8TQ100G-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95221					
Deat and discuss in factors at least	TO-220AC PbF	www.vishay.com/doc?95224			
Part marking information	TO-220AC -N3	www.vishay.com/doc?95068			
SPICE model		www.vishay.com/doc?95291			



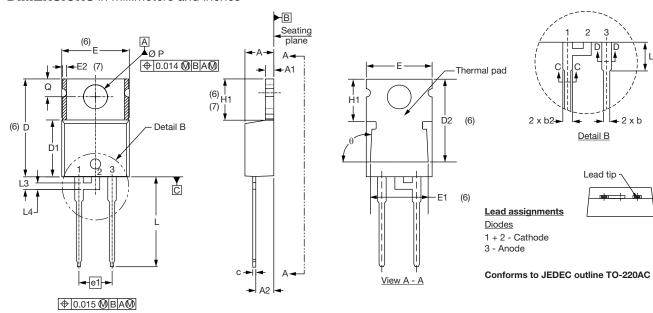


Outline Dimensions

Vishay Semiconductors

TO-220AC

DIMENSIONS in millimeters and inches



SYMBOL MILLIMETE		MILLIMETERS INCHES		NOTES	
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	

Notes

- $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- $^{(7)}$ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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